

## Description

### JMP N-channel Enhancement Mode Power MOSFET

#### Features

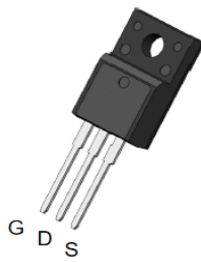
- 600V, 10A  
 $R_{DS(ON)} < 0.90\Omega @ V_{GS} = 10V$
- Fast Switching
- Improved dv/dt Capability

#### Applications

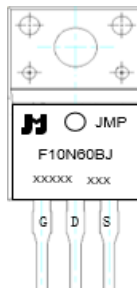
- Load Switch
- PWM Application
- Power Management



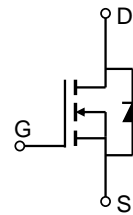
*100% UIS TESTED!*  
*100% ΔVds TESTED!*



TO-220FP-3L Top View



Marking and Pin Assignment



Schematic Diagram

## Package Marking and Ordering Information

Device Marking	Device	Outline	Package	TUBE (pcs)	Inner Box (pcs)	Per Carton (pcs)
JMPF10N60BJ	JMPF10N60BJ	TUBE	TO-220FP-3L	50	1000	5000

## Absolute Maximum Ratings (@ $T_C = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Value	Units
$V_{DS}$	Drain-to-Source Voltage	600	V
$V_{GS}$	Gate-to-Source Voltage	$\pm 30$	V
$I_D$	Continuous Drain Current	$T_C = 25^\circ\text{C}$	10
		$T_C = 100^\circ\text{C}$	7
$I_{DM}$	Pulsed Drain Current <sup>(1)</sup>	40	A
$E_{AS}$	Single Pulsed Avalanche Energy <sup>(2)</sup>	414	mJ
$P_D$	Power Dissipation	$T_C = 25^\circ\text{C}$	27
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient <sup>(3)</sup>	52	°C/W
$R_{\theta JC}$	Thermal Resistance, Junction to Case	4.7	
$T_J, T_{STG}$	Junction & Storage Temperature Range	-55 to 150	°C



## Electrical Characteristics (T<sub>J</sub> = 25°C unless otherwise specified)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
<b>Off Characteristics</b>						
V <sub>(BR)DSS</sub>	Drain-Source Breakdown Voltage	I <sub>D</sub> = 250μA, V <sub>GS</sub> = 0V	600	-	-	V
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> = 600V, V <sub>GS</sub> = 0V	-	-	1.0	μA
I <sub>GSS</sub>	Gate-Body Leakage Current	V <sub>DS</sub> = 0V, V <sub>GS</sub> = ±30V	-	-	±100	nA
<b>On Characteristics</b>						
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA	2	3	4	V
R <sub>DS(ON)</sub>	Static Drain-Source ON-Resistance <sup>(4)</sup>	V <sub>GS</sub> = 10V, I <sub>D</sub> = 5A	-	0.69	0.90	Ω
<b>Dynamic Characteristics</b>						
C <sub>iss</sub>	Input Capacitance	V <sub>GS</sub> = 0V, V <sub>DS</sub> = 25V, f = 1MHz	-	1602	-	pF
C <sub>oss</sub>	Output Capacitance		-	142	-	pF
C <sub>rss</sub>	Reverse Transfer Capacitance		-	17	-	pF
Q <sub>g</sub>	Total Gate Charge	V <sub>GS</sub> = 0 to 10V V <sub>DS</sub> = 300V, I <sub>D</sub> = 10A	-	34	-	nC
Q <sub>gs</sub>	Gate Source Charge		-	8.9	-	nC
Q <sub>gd</sub>	Gate Drain("Miller") Charge		-	11	-	nC
<b>Switching Characteristics</b>						
t <sub>d(on)</sub>	Turn-On DelayTime	V <sub>GS</sub> = 10V, V <sub>DD</sub> = 310V I <sub>D</sub> = 10A, R <sub>GEN</sub> = 24Ω	-	25	-	ns
t <sub>r</sub>	Turn-On Rise Time		-	34	-	ns
t <sub>d(off)</sub>	Turn-Off DelayTime		-	99	-	ns
t <sub>f</sub>	Turn-Off Fall Time		-	41	-	ns
<b>Drain-Source Diode Characteristics and Max Ratings</b>						
I <sub>S</sub>	Maximum Continuous Drain to Source Diode Forward Current		-	-	10	A
I <sub>SM</sub>	Maximum Pulsed Drain to Source Diode Forward Current		-	-	40	A
V <sub>SD</sub>	Drain to Source Diode Forward Voltage	V <sub>GS</sub> = 0V, I <sub>S</sub> = 10A	-	-	1.2	V
t <sub>rr</sub>	Body Diode Reverse Recovery Time	I <sub>F</sub> = 10A, di/dt = 100A/us	-	480	-	ns
Q <sub>rr</sub>	Body Diode Reverse Recovery Charge		-	4.5	-	μC

- Notes:
1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature.
  2. E<sub>AS</sub> condition: Starting T<sub>J</sub>=25C, V<sub>DD</sub>=50V, V<sub>G</sub>=10V, R<sub>G</sub>=25ohm, L=10mH, I<sub>AS</sub>=9A
  3. RθJA is measured with the device mounted on a minimum recommended pad of 2oz copper FR4 PCB
  4. Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 0.5%.



## Typical Performance Characteristics

Figure 1: Output Characteristics

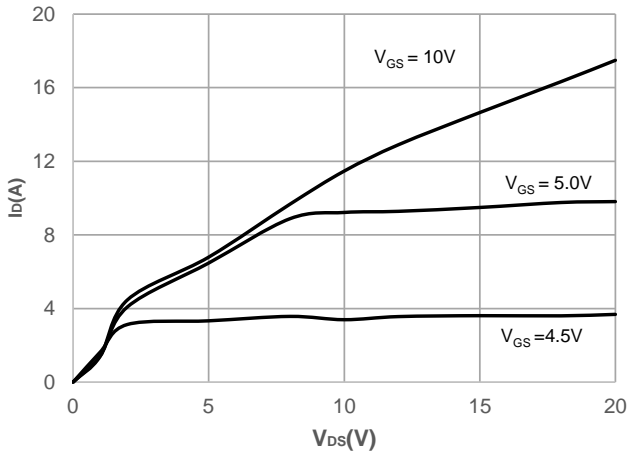


Figure 2: Typical Transfer Characteristics

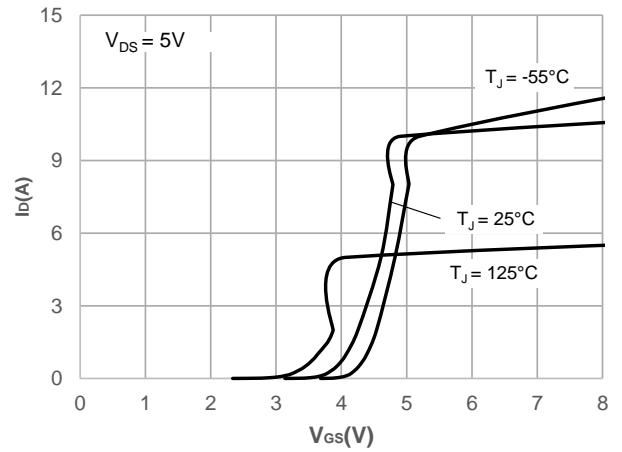


Figure 3: On-resistance vs. Drain Current

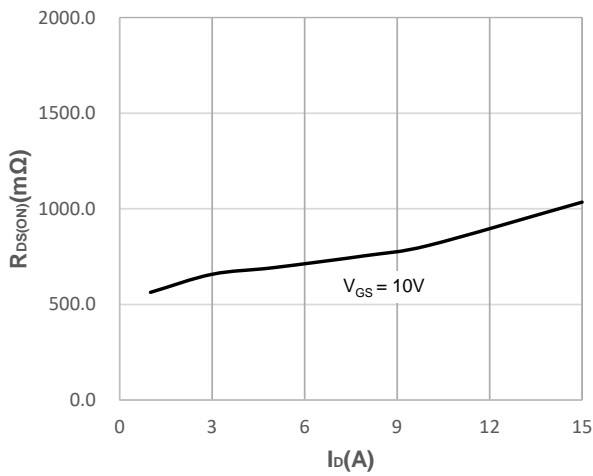


Figure 4: Body Diode Characteristics

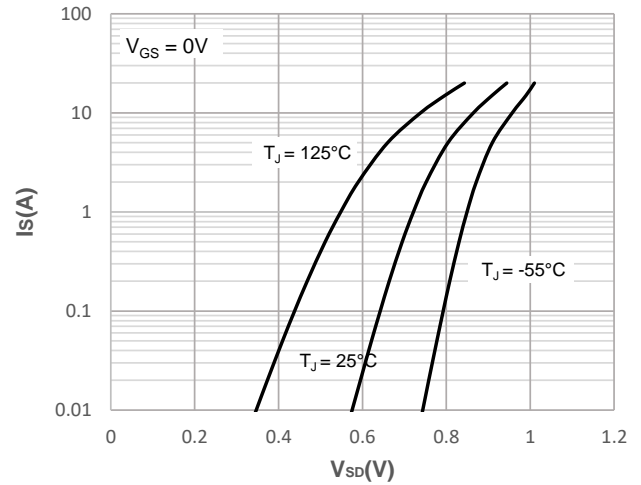


Figure 5: Gate Charge Characteristics

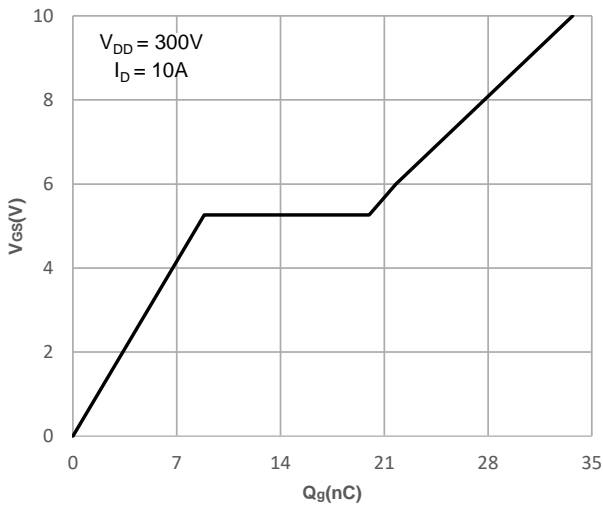
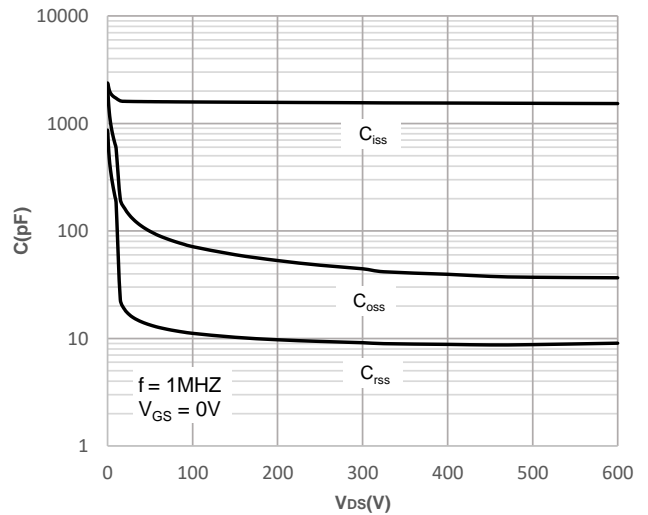


Figure 6: Capacitance Characteristics



## Typical Performance Characteristics

Figure 7: Normalized Breakdown voltage vs. Junction Temperature

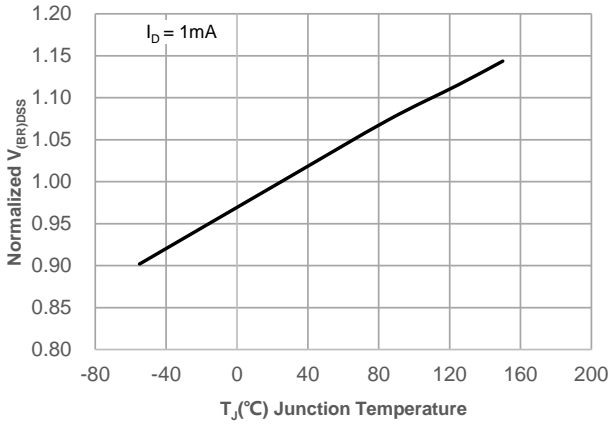


Figure 8: Normalized on Resistance vs. Junction Temperature

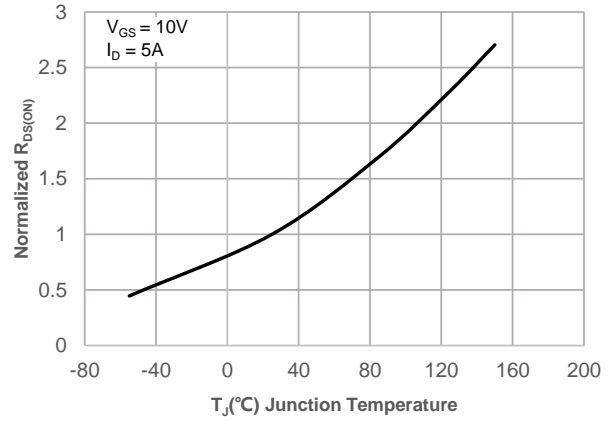


Figure 9: Maximum Safe Operating Area

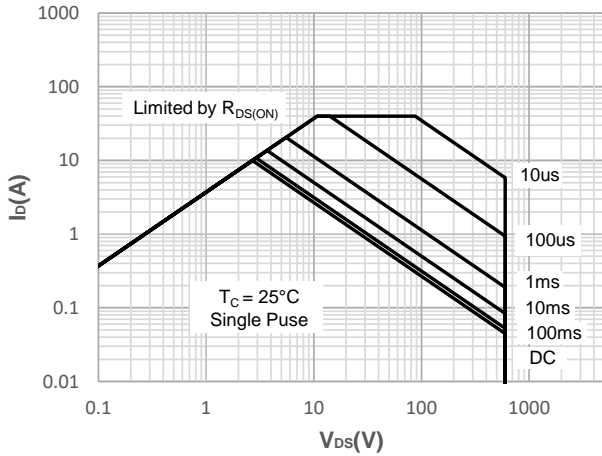


Figure 10: Maximum Continuous Driain Current vs. Case Temperature

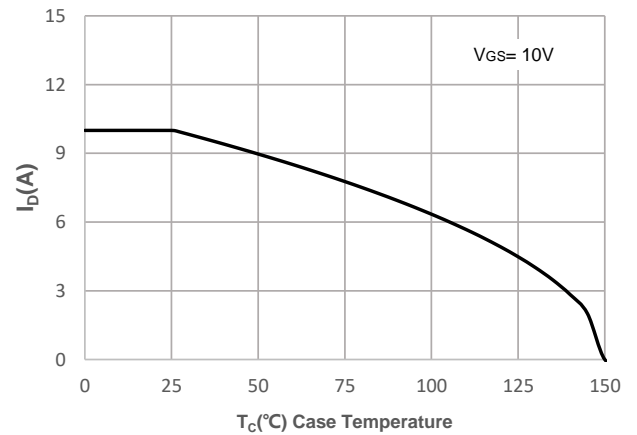


Figure 11: Normalized Maximum Transient Thermal Impedance

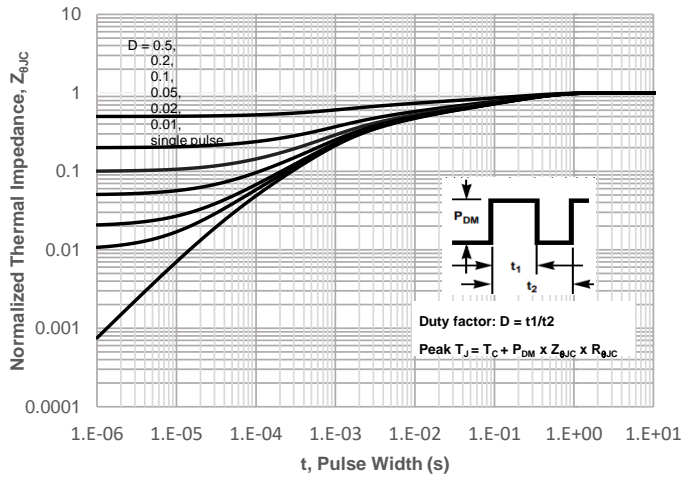
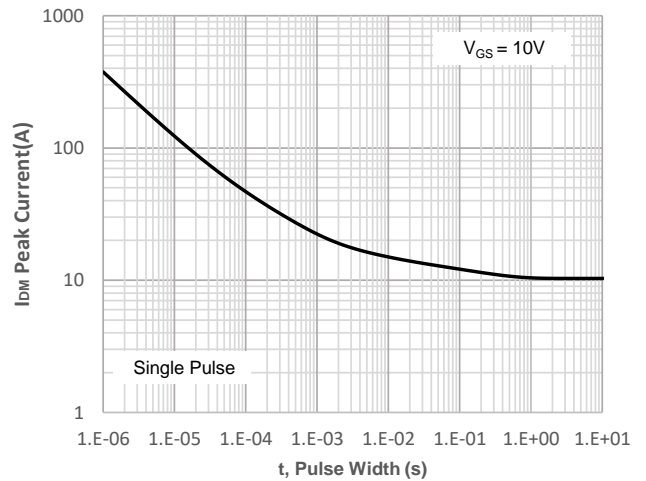


Figure 12: Peak Current Capacity



## Test Circuit

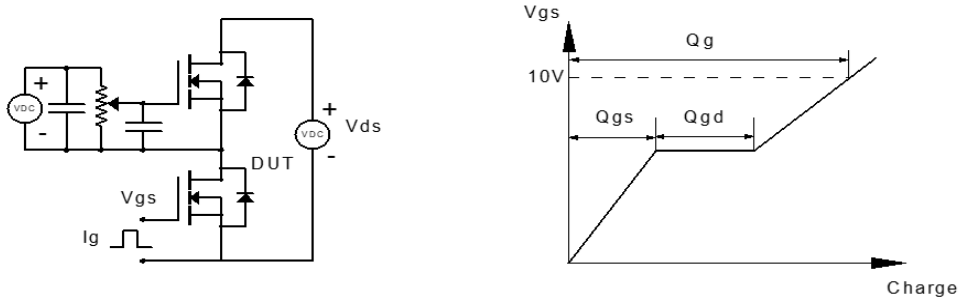


Figure 1: Gate Charge Test Circuit & Waveform

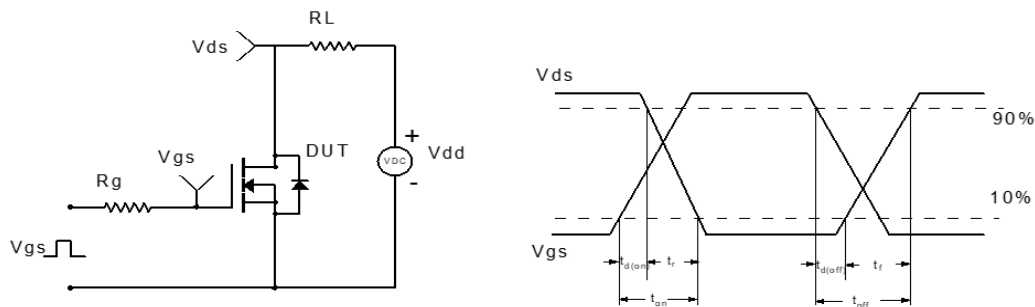


Figure 2: Resistive Switching Test Circuit & Waveform

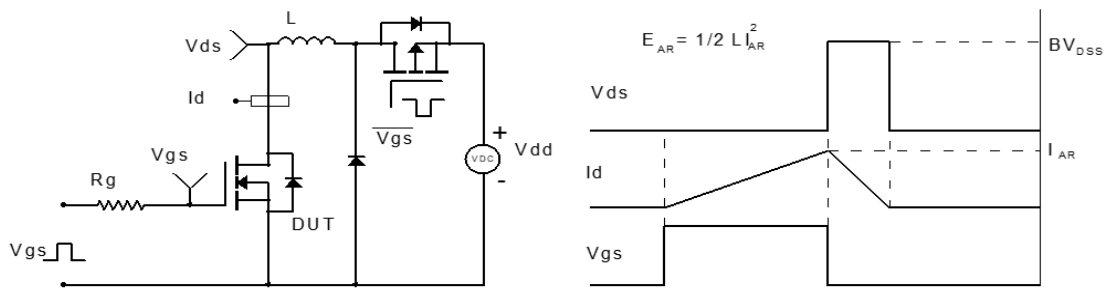


Figure 3: Unclamped Inductive Switching Test Circuit & Waveform

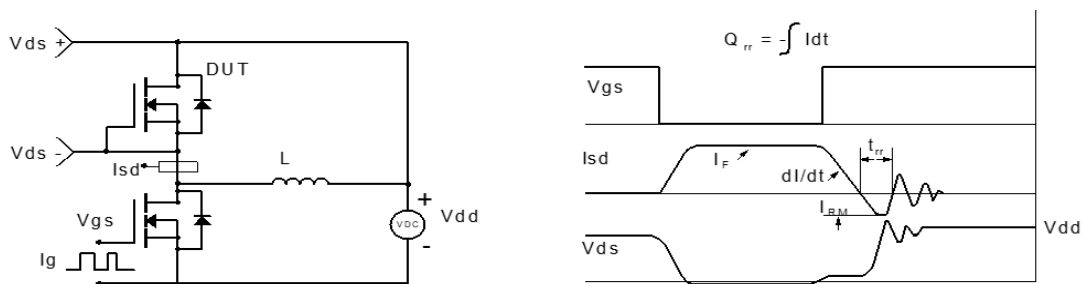
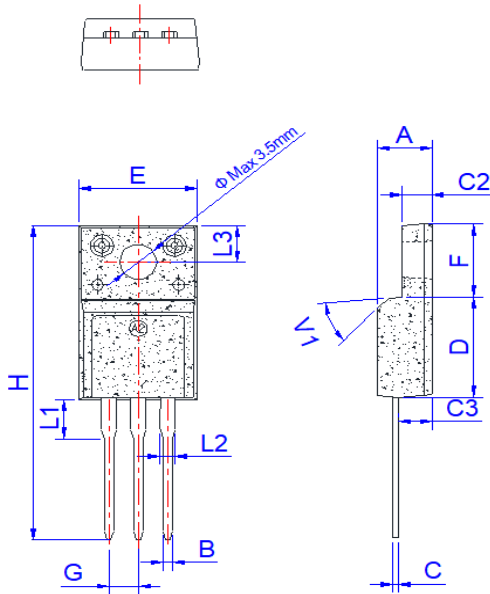


Figure 4: Diode Recovery Test Circuit & Waveform

## Package Mechanical Data(TO-220FP-3L)



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.50		4.90	0.177		0.193
B	0.74	0.80	0.83	0.029	0.031	0.033
C	0.47		0.65	0.019		0.026
C2	2.45		2.75	0.096		0.108
C3	2.60		3.00	0.102		0.118
D	8.80		9.30	0.346		0.366
E	9.80		10.4	0.386		0.410
F	6.40		6.80	0.252		0.268
G		2.54			0.1	
H	28.0		29.8	1.102		1.173
L1		3.63			0.143	
L2	1.14		1.70	0.045		0.067
L3		3.30			0.130	
V1		45°			45°	

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